IN THE CLAIMS:

Please amend Claims 3-6, 8, 9, 17, 18 and 26, as follows:

3 (amended). A multi-chip package type semiconductor device, as claimed in claim 2, further comprising a first metal bump formed on the conductive relay pad in the first area and a second metal bump formed on the second terminal pad, wherein a first bond as a beginning connection of the first bonding wire is preformed at the first terminal pad and a second bond as an ending connection of the first bonding wire is made at the first conductive pattern, wherein a first bond as a beginning connection of the second bonding wire is preformed at the second conductive pattern and a second bond as an ending connection of the second bonding wire is made at the first metal bump, and wherein a first bond as a beginning connection of the third bonding wire is preformed at the conductive relay pad in the second area and a second bond as an ending connection of the third bonding wire is made at the second metal bump.

C1

4 (amended). A multi-chip package type semiconductor device, as claimed in claim 2, further comprising a metal bump formed on the conductive relay pad in the second area, wherein a first bond as a beginning connection of the first bonding wire is preformed at the first terminal pad and a second bond as an ending connection of the first bonding wire is made at the first conductive pattern, wherein a first bond as a beginning connection of the second bonding wire is preformed at the conductive relay pad in the first area and a second bond as an ending connection of the second bonding wire is made at the second conductive pattern, and wherein a first bond as a beginning connection of the third bonding wire is preformed at the second terminal pad and a

second bond as an ending connection of the third bonding wire is made at the metal bump.

5 (amended). A multi-chip package type semiconductor device, as claimed in claim 3, wherein the conductive relay pad is rectangularly-shaped, and is formed on a periphery of the first semiconductor chip, and a longer side of the rectangularly-shaped conductive relay pad is parallel to a side of the first semiconductor chip.

C1

6 (amended). A multi-chip package type semiconductor device, as claimed in claim 3, wherein the conductive relay pad is rectangularly-shaped, and is formed on a periphery of the first semiconductor chip, and a shorter side of the rectangularly-shaped conductive relay pad is parallel to a side of the first semiconductor chip.

8 (amended). A multi-chip package type semiconductor device, as claimed in claim 4, wherein the conductive relay pad is rectangularly-shaped, and is formed on a periphery of the first semiconductor chip, and a longer side of the rectangularly-shaped conductive relay pad is parallel to a side of the first semiconductor chip.

C2

9 (amended). A multi-chip package type semiconductor device, as claimed in claim 4, wherein the conductive relay pad is rectangularly-shaped, and is formed on a periphery of the first semiconductor chip, and a shorter side of the rectangularly-shaped conductive relay pad is parallel to a side of the first semiconductor chip.

17 (amended). A multi-chip package type semiconductor device, as claimed in claim 16, further comprising a first metal bump formed on the conductive relay pad and a second metal bump formed on the second terminal pad, wherein a first bond as a beginning connection of the first bonding wire is preformed at the first terminal pad and a second bond as an ending connection of the first bonding wire is made at the first conductive pattern, wherein a first bond as a beginning connection of the second bonding wire is preformed at the second conductive pattern and a second bond as an ending connection of the second bonding wire is made at the first metal bump, and wherein a first bond as a beginning connection of the third bonding wire is preformed at the first metal bump and a second bond as an ending connection of the third bonding wire is made at the second metal bump.

C3

18 (amended). A multi-chip package type semiconductor device, as claimed in claim 16, further comprising a metal bump formed on the conductive relay pad, wherein a first bond as a beginning connection of the first bonding wire is preformed at the first terminal pad and a second bond as an ending connection of the first bonding wire is made at the first conductive pattern, wherein a first bond as a beginning connection of the second bonding wire is preformed at the conductive pattern and a second bond as an ending connection of the second bonding wire is made at the metal bump, and wherein a first bond as a beginning connection of the third bonding wire is preformed at the second terminal pad and a second bond as an ending connection of the third bonding wire is made at the metal bump.